

Initial Product/Process Change Notification Document #: IPCN25156Z Issue Date: 14 Dec 2022

Title of Change:	WDFN6 Assembly Transfer from UTAC, Thailand to Seremban Malaysia Site 1.			
Proposed Changed Material First Ship Date:	30 Oct 2023 or earlier if approved by customer			
Current Material Last Order Date:	N/A Orders received after the Current Material Last Order Date expiration are to be considered as orders for new changed material as described in this PCN. Orders for current (unchanged) material after this date will be per mutual agreement and current material inventory availability.			
Current Material Last Delivery Date:	N/A The Current Material Last Delivery Date may be subject to change based on build and depletion of the current (unchanged) material inventory			
Product Category:	Active components – Discrete components			
Contact information:	Contact your local onsemi Sales Office or Bernard	dRajVellangani.Pelevindran@onsemi.com		
PCN Samples Contact:	Contact your local onsemi Sales Office to place sample order. Sample requests are to be submitted no later than 45 days after publication of this change notification. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.			
Additional Reliability Data:	Contact your local onsemi Sales Office or MohdAzizi.Azman@onsemi.com			
Type of Notification:	This is an Initial Product/Process Change Notification (IPCN) sent to customers. An IPCN is an advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan. The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN). This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 6 months prior to implementation of the change. In case of questions, contact < <u>PCN.Support@onsemi.com</u> >.			
Change Category				
Category	Type of Change			
Equipment	Production from a new equipment/tool which uses the same basic technology (replacement equipment or extension of existing equipment pool) without change of process.			
Process - Assembly	Move of all or part of assembly to a different location/site/subcontractor., Change of mold compound, Change of direct material supplier, Change of wire bonding			
Description and Purpose:				
	From	То		
Assembly Site	UTAC, Thailand	Seremban Malaysia Site 1. (SBN Site 1)		
LeadFrame	SFS Wettable Flank	Step Cut Wettable Flank		
	1. ABLETHERM 8600 CONDUCTIVE (NSV60101DMTWTBG, NSV60200DMTWTBG,	CRM1084P (All Device)		



	Bond Wire	1.3mil Gold Wire		1.3mil Palladium Coated Copper Wir	
Mold Compound		 Sumitomo G770HCD (NSV60101DMTWTBG, NSV60200DMTWTBG, NSV60200SMTWTBG, NSV60201SMTWTBG). MC G700LTD (NSV20200DMTWTBG, NSV20201DMTWTBG) 		MC EME-G720D Type (All Device)	
eason / Moti	vation for Change:	Process/Materials Ch	ange		
	vation for change.				
Anticipated impact on fit, form, function, reliability, product safety or manufacturability:		The device will be qualified and validated based on the same Product Specification. No anticipated impacts.			
ites Affected:			1		
nsemi Sites		External Foundry/Subcon Sites			
nsemi Seremba	n, Malaysia	None			
Aarking of Par eliability Data	rts/ Traceability of Change: a Summary:	changed material m	ay be identified by lot code or dat	e code	
eliability Data V DEVICE NAM MS: S86916(NS		/60200DMTWTBG		e code	
eliability Data V DEVICE NAM MS: S86916(NS	a Summary: IE: NSV60101DMTWTBG & NSV 6V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm	/60200DMTWTBG		e code	Interval
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF	a Summary: IE: NSV60101DMTWTBG & NSV 6V60101DMTWTBG) & S74843,	/60200DMTWTBG . \$73609(NSV60200DM	тwтвg)		Interval 2016 hrs
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF Test	a Summary: IE: NSV60101DMTWTBG & NSV 6V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm Specification	/60200DMTWTBG 573609(NSV60200DM Tj = Max rate Tj for	TWTBG) Condition device, bias = 100% of rated V fo		
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF Test HTRB	a Summary: IE: NSV60101DMTWTBG & NSV 5V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm Specification JESD22-A108	/60200DMTWTBG 573609(NSV60200DM Tj = Max rate Tj for Ta =	TWTBG) Condition	or Q 101 Rev D	2016 hrs
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF Test HTRB HTSL	a Summary: IE: NSV60101DMTWTBG & NSV 6V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm Specification JESD22-A108 JESD22-A103	/60200DMTWTBG 573609(NSV60200DM Tj = Max rate Tj for Ta =	TWTBG) Condition device, bias = 100% of rated V fo Max rate storage temp for device	or Q 101 Rev D	2016 hrs 2016 hrs
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF Test HTRB HTRL ELFR	A Summary: IE: NSV60101DMTWTBG & NSV 6V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm Specification JESD22-A108 JESD22-A103 AECQ100-008	/60200DMTWTBG 573609(NSV60200DM Tj = Max rate Tj for Ta = may uti	TWTBG) Condition device, bias = 100% of rated V for Max rate storage temp for device lize either HTGB or HTRB conditio	or Q 101 Rev D Ins	2016 hrs 2016 hrs
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF Test HTRB HTRB HTSL ELFR PC	a Summary: IE: NSV60101DMTWTBG & NSV 6V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm Specification JESD22-A108 JESD22-A103 AECQ100-008 J-STD-020 JESD-A113	/60200DMTWTBG . \$73609(NSV60200DM Tj = Max rate Tj for Ta =I may uti 130°C, 85% RH	TWTBG) Condition device, bias = 100% of rated V fo Max rate storage temp for device lize either HTGB or HTRB conditio IR reflow at 260C	or Q 101 Rev D Ins 100V max	2016 hrs 2016 hrs 48 hrs
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF Test HTRB HTRL ELFR PC HAST + PC	A Summary: IE: NSV60101DMTWTBG & NSV 6V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm Specification JESD22-A108 JESD22-A103 AECQ100-008 J-STD-020 JESD-A113 JESD22-A110	/60200DMTWTBG . \$73609(NSV60200DM Tj = Max rate Tj for Ta =I may uti 130°C, 85% RH	TWTBG) Condition device, bias = 100% of rated V fo Max rate storage temp for device lize either HTGB or HTRB conditio IR reflow at 260C , 18.8psig, bias 80% of rated V or	or Q 101 Rev D Ins 100V max	2016 hrs 2016 hrs 48 hrs 192 hrs
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF Test HTRB HTSL ELFR PC HAST + PC H3TRB + PC	A Summary: IE: NSV60101DMTWTBG & NSV 5V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm Specification JESD22-A108 JESD22-A103 AECQ100-008 J-STD-020 JESD-A113 JESD22-A100 JESD22-A101	/60200DMTWTBG 573609(NSV60200DM Tj = Max rate Tj for Ta =I may uti 130°C, 85% RH Temp	TWTBG) Condition device, bias = 100% of rated V for Max rate storage temp for device lize either HTGB or HTRB conditio IR reflow at 260C , 18.8psig, bias 80% of rated V or = +85°C; RH = 85%, 80% rated Vol	or Q 101 Rev D Ins 100V max	2016 hrs 2016 hrs 48 hrs 192 hrs 2016 hrs
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF Test HTRB HTSL ELFR PC HAST + PC H3TRB + PC TC + PC	A Summary: IE: NSV60101DMTWTBG & NSV 5V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm Specification JESD22-A108 JESD22-A108 JESD22-A103 AECQ100-008 J-STD-020 JESD-A113 JESD22-A100 JESD22-A101 JESD22-A104	/60200DMTWTBG S73609(NSV60200DM Tj = Max rate Tj for Ta =I may uti 130°C, 85% RH Temp Ter	TWTBG) Condition device, bias = 100% of rated V for Max rate storage temp for device lize either HTGB or HTRB conditio IR reflow at 260C , 18.8psig, bias 80% of rated V or = +85°C; RH = 85%, 80% rated Vol Temp = -55°C to +150°C	or Q 101 Rev D Ins 100V max It	2016 hrs 2016 hrs 48 hrs 192 hrs 2016 hrs 2000 cycle
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF Test HTRB HTSL ELFR PC HAST + PC H3TRB + PC TC + PC UHAST + PC	A Summary: IE: NSV60101DMTWTBG & NSV 5V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm Specification JESD22-A108 JESD22-A108 JESD22-A103 AECQ100-008 J-STD-020 JESD-A113 JESD22-A110 JESD22-A101 JESD22-A101 JESD22-A104 JESD22-A118 MIL STD750, M 1037	/60200DMTWTBG S73609(NSV60200DM Tj = Max rate Tj for Ta =I may uti 130°C, 85% RH Temp Ter	TWTBG) Condition device, bias = 100% of rated V for Max rate storage temp for device lize either HTGB or HTRB condition IR reflow at 260C , 18.8psig, bias 80% of rated V or = +85°C; RH = 85%, 80% rated Vol Temp = -55°C to +150°C np = 130C, RH=85%, ~ 18.8 psig	or Q 101 Rev D Ins 100V max It	2016 hrs 2016 hrs 48 hrs 192 hrs 2016 hrs 2000 cycle 96 hrs
eliability Data V DEVICE NAM MS: S86916(NS ACKAGE: WDF Test HTRB HTSL ELFR PC HAST + PC HAST + PC TC + PC UHAST + PC IOL+PC	A Summary: IE: NSV60101DMTWTBG & NSV 5V60101DMTWTBG) & S74843, N6 2.0mmx2.0mmx0.75mm Specification JESD22-A108 JESD22-A108 JESD22-A103 AECQ100-008 J-STD-020 JESD-A113 JESD22-A110 JESD22-A101 JESD22-A104 JESD22-A104 JESD22-A104 AECQ101	/60200DMTWTBG S73609(NSV60200DM Tj = Max rate Tj for Ta =I may uti 130°C, 85% RH Temp Ter	TWTBG) Condition device, bias = 100% of rated V for Max rate storage temp for device lize either HTGB or HTRB conditio IR reflow at 260C , 18.8psig, bias 80% of rated V or = +85°C; RH = 85%, 80% rated Vol Temp = -55°C to +150°C np = 130C, RH=85%, ~ 18.8 psig 100°C max, xxx min Ton=Toff (pk	or Q 101 Rev D Ins 100V max It	2016 hrs 2016 hrs 48 hrs 192 hrs 2016 hrs 2000 cycle 96 hrs

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Electrical Characteristics Summary:

Electrical characteristics are not impacted.

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the <u>PCN Customized Portal</u>.

Current Part Number	New Part Number	Qualification Vehicle
NSV60201SMTWTBG	NA	NSV60101DMTWTBG
NSV60200SMTWTBG	NA	NSV60200DMTWTBG
NSV60200DMTWTBG	NA	NSV60200DMTWTBG
NSV60101DMTWTBG	NA	NSV60101DMTWTBG
NSV20201DMTWTBG	NA	NSV60101DMTWTBG
NSV20200DMTWTBG	NA	NSV60200DMTWTBG